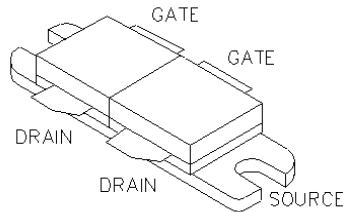




General Description

This device is part of Polyfet's latest family of 28VDC LDMOS devices. Being an unmatched device and having low capacitances makes it ideal for broad band applications such as communications and broadcast. It is also suitable for various narrow band applications. Employing back-to-back gate diodes for enhanced ESD protection and having a high drain breakdown voltage makes this device highly rugged. The suitable frequency range of this device is 1-1100MHz



SILICON GATE ENHANCEMENT MODE

RF POWER LDMOS TRANSISTOR

200.0 Watts Push - Pull

Package Style LR

HIGH EFFICIENCY, LINEAR

HIGH GAIN, LOW NOISE

ROHS COMPLIANT

ABSOLUTE MAXIMUM RATINGS (T = 25 °C)

Total Device Dissipation	Junction to Case Thermal Resistance	Maximum Junction Temperature	Storage Temperature	DC Drain Current	Drain to Gate Voltage	Drain to Source Voltage	Gate to Source Voltage
420 Watts	0.40 °C/W	200 °C	-65 °C to 150 °C	18.0 A	80 V	80 V	+ 11 V - 9 V

RF CHARACTERISTICS (200.0 WATTS OUTPUT)

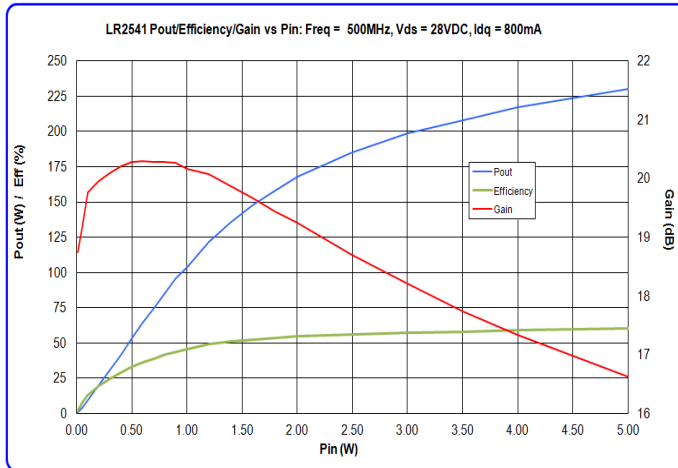
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Gps	Common Source Power Gain	16			dB	Idq = 0.80 A, Vds = 28.0 V, F = 500 MHz
η	Drain Efficiency		60		%	Idq = 0.80 A, Vds = 28.0 V, F = 500 MHz
VSWR	Load Mismatch Tolerance			20:1	Relative	Idq = 0.80 A, Vds = 28.0 V, F = 500 MHz

ELECTRICAL CHARACTERISTICS (EACH SIDE)

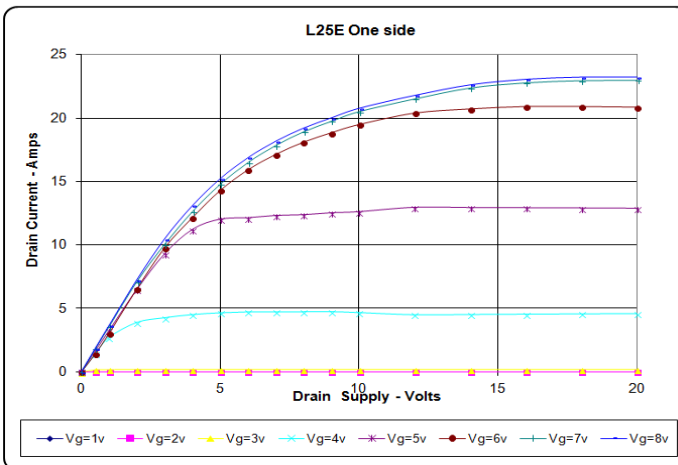
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Bvdss	Drain Breakdown Voltage	80			V	Ids = 5.00 mA, Vgs = 0V
Idss	Zero Bias Drain Current			2.0	mA	Vds = 28.0 V, Vgs = 0V
Igss	Gate Leakage Current			1	uA	Vds = 0V Vgs = 10V
Vgs	Gate Bias for Drain Current	2		5	V	Ids = 0.20 A, Vgs = Vds
gM	Forward Transconductance		7.5		Mho	Vds = 10V, Vgs = 5V
Rdson	Saturation Resistance		0.30		Ohm	Vgs = 10 V, Ids = 15.00 A
Idsat	Saturation Current		21.00		Amp	Vgs = 10 V, Vds = 10V
Ciss	Common Source Input Capacitance		122.0		pF	Vds = 28.0 Vgs = 0V, F = 1 MHz
Crss	Common Source Feedback Capacitance		2.0		pF	Vds = 28.0 Vgs = 0V, F = 1 MHz
Coss	Common Source Output Capacitance		45.0		pF	Vds = 28.0 Vgs = 0V, F = 1 MHz

LR2541

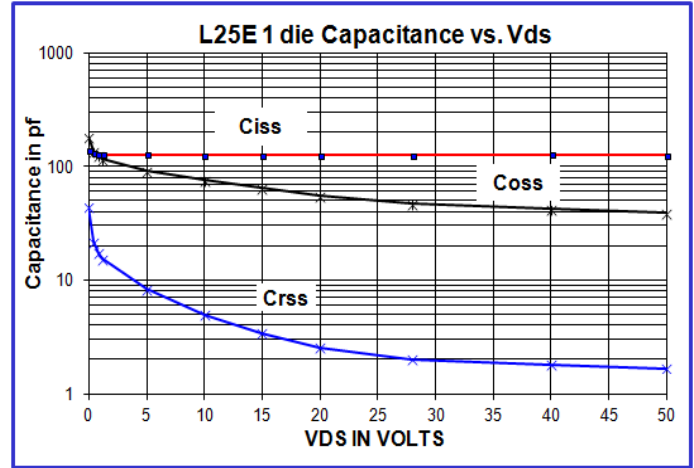
POUT VS PIN GRAPH



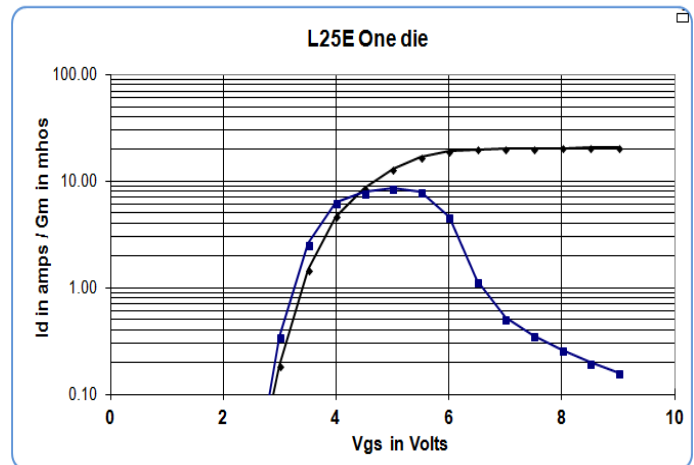
IV CURVE



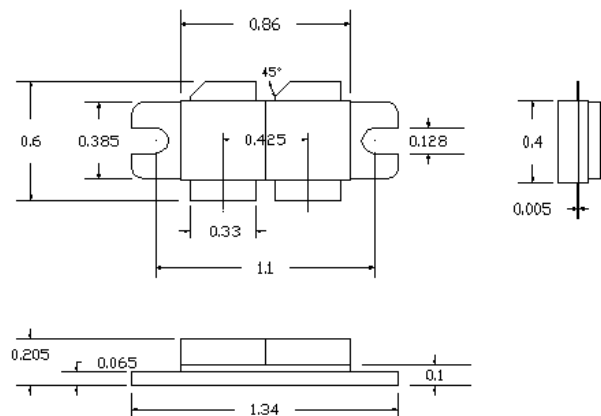
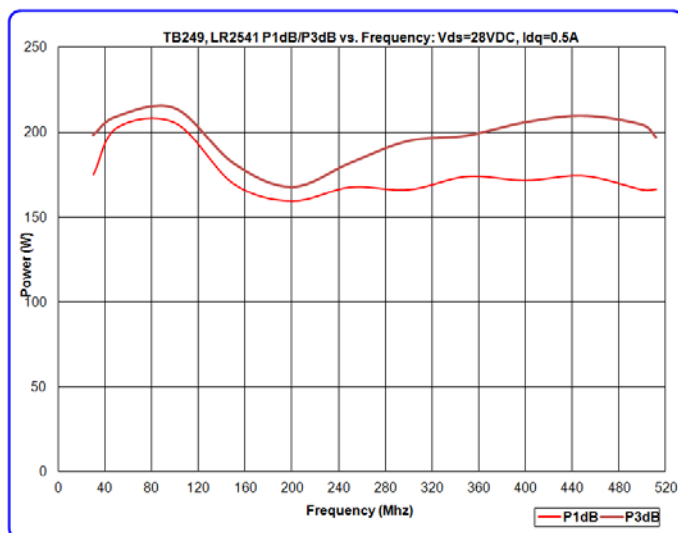
CAPACITANCE VS VOLTAGE



ID & GM VS VGS



PACKAGE DIMENSIONS IN INCHES



POLYFET LR PACKAGE
Tolerance .XX +/-0.01 .XXX +/-0.005 inches